

isc N-Channel Mosfet Transistor

BUZ32

• FEATURES

- 9.5A, 200V
- $R_{DS(ON)} = 0.400 \Omega$
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

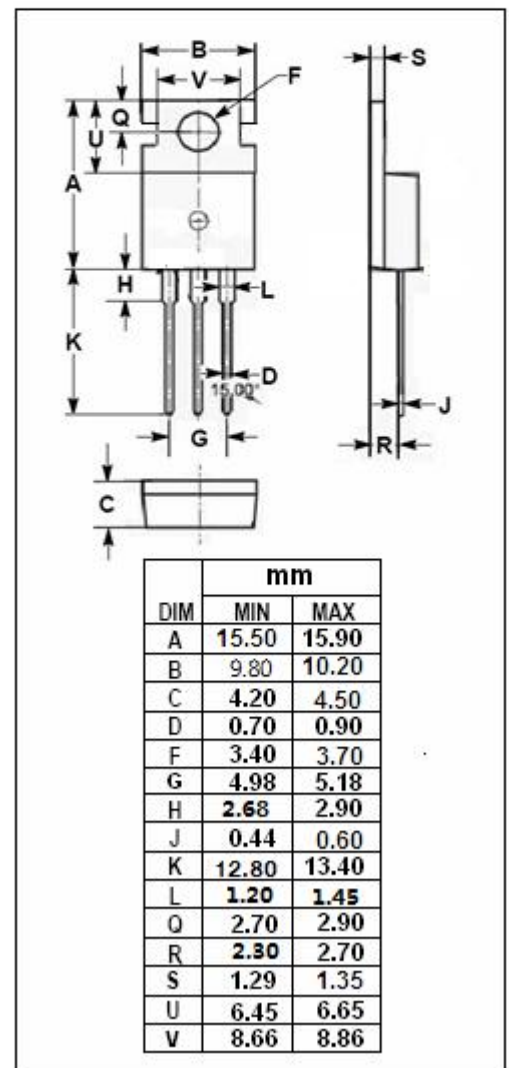
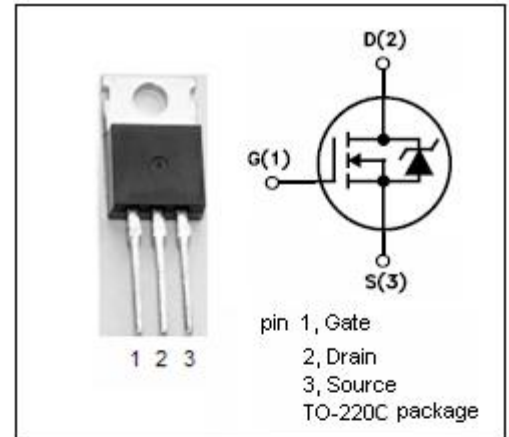
Designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. This type can be operated directly from integrated circuits.

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage ($V_{GS}=0$)	200	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=55^\circ\text{C}$	9.5	A
I_{DM}	Drain Current-Single Pulsed	38	A
P_{tot}	Total Dissipation@ $TC=25^\circ\text{C}$	75	W
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.67	$^\circ\text{C/W}$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	75	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=0.25\text{mA}$	200			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=1\text{mA}$	2.1		4.0	V
V_{SD}	Diode Forward On-voltage	$I_S=19\text{A}; V_{GS}=0$			1.7	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=4.5\text{A}$			0.4	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=200\text{V}; V_{GS}=0$			250	μA
Gfs	Forward Transconductance	$V_{DS}=25\text{V}; I_D=4.5\text{A}$	2.2			S
$t_{d(on)}$	Turn-on Delay Time	$V_{GS}=10\text{V};$ $I_D=2.9\text{A};$ $V_{DD}=30\text{V};$ $R_{GS}=50\Omega$			45	ns
t_r	Rise Time				60	
$t_{d(off)}$	Turn-off Delay Time				140	
t_f	Fall Time				80	

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